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# TABLE OF CONTENTS

The RADECS 2008 Workshop Overview . . . . .	8
RADECS 2008 Organization Committee . . . . .	9
Industrial Exhibition . . . . .	10
Partners . . . . .	11
International Technical Committee . . . . .	12
Official Reviewers . . . . .	13
RADECS 2008 Awards . . . . .	14
Invited Talks . . . . .	15

## SESSION A. RADIATION EFFECTS IN DEVICES AND ICs

A1. <b>TID Sensitivity of NAND Flash Memory Building Blocks</b> . . . . .	34
M. Bagatin, G. Cellere, A. Paccagnella, A. Visconti, and S. Beltrami	
A4. <b>Impact of Proton Irradiation on the RF Performance of 65 nm SOI CMOS Technology</b> . . . . .	47
A. Madan, S. D. Phillips, J. D. Cressler, P. W. Marshall, Q. Liang, and G. Freeman	
A5. <b>Design, Assessment and Modeling of an Integrated 0.4 <math>\mu</math>m SiGe Bipolar VCSEL Driver under <math>\gamma</math>-Radiation</b> . . . . .	53
P. Leroux, W. De Cock, M. Van Uffelen, M. Steyaert	
PA2.    S. Díez, M. Ullán, F. Campabadal, M. Lozano, G. Pellegrini, I. Mandić, D. Knoll, and B. Heinemann	
<b>Proton Radiation Test of DC/DC Converter With High Voltage Output</b> . . . . .	70
St. Scherrer, W. Hajdas, U. Grossner, and N. Schlumpf	
PA3.    R. L. Pease	
<b>2008 Update to the ELDRS Bipolar Linear Circuit Data Compendium</b> . . . . .	75

## SESSION B. SEEs; DEVICES AND ICs

B1. <b>A Self-Checking Scheme to Mitigate Single Event Upset Effects in SRAM-based FPAs</b> . . . . .	90
T. R. Balen, F. Leite, F. G. L. Kastensmidt, and M. Lubaszewski	
B3. <b>Factors Impacting the Temperature Dependence of Soft Errors in Commercial SRAMs</b> . . . . .	100
M. Bagatin, S. Gerardin, A. Paccagnella, C. Andreani, G. Gorini, A. Pietropaolo, S. P. Platt, and C. D. Frost	
B4. <b>Gate Rupture in Ultra-thin Gate Oxides Irradiated with Heavy Ions</b> . . . . .	107
M. Silvestri, S. Gerardin, A. Paccagnella, and G. Ghidini	

<b>B6.</b>	<b>Single-Event Upsets in Photodiodes for Multi-Gb/s Data Transmission</b>	120
	A. J. Pacheco, J. Troska, L. Amaral, S. Dris, D. Ricci, C. Sigaud, F. Vasey, and P. Vichoudis	
<b>PB3.</b>	<b>SEU Effects on Static and Clocked Cascade Voltage Switch Logic (CVSL) Circuits</b>	136
	H. Hatano	
<b>PB6LN.</b>	<b>Pulsed Laser SEU Cross-Section Measurement Using Coincidence Detectors</b>	147
	F. R. Palomo, J. M. Mogollón, J. Nápoles, H. Guzmán-Miranda, A. P. Vega-Leal, M. A. Aguirre, P. Moreno, C. Méndez, and J. R. Vázquez de Aldana	
<b>PB8LN.</b>	<b>Robustness Analysis of Soft Error Accumulation in SRAM-FPGAs Using FLIPPER and STAR/RoRA</b>	157
	M. Alderighi, F. Casini, S. D'Angelo, M. Mancini, D. Merodio-Codinachs, S. Pastore, G. Sorrenti, L. Sterpone, R. Weigand, and M. Violante	

## SESSION C. SEEs; MECHANISMS AND MODELLING

<b>C2.</b>	<b>A New Technique for SET Pulse Width Measurement in Chains of Inverters Using Pulsed Laser Irradiation</b>	169
	V. Ferlet-Cavrois, D. McMorrow, D. Kobayashi, N. Fel, J. S. Melinger, P. Paillet, V. Pouget, F. Essely, J. Baggio, S. Girard, R. S. Flores, J. R. Schwank, P. E. Dodd, M. R. Shaneyfelt, K. Hirose, H. Saito	
<b>C4.</b>	<b>SEU Rates in Atmospheric Environments: Variations Due to Cross-Section Fits and Environment Models</b>	180
	A. D. P. Hands, C. S. Dyer, and F. Lei	
<b>PC2.</b>	<b>Modeling the Effects of Broadening and Degradation of Single Event Transient Pulses in Integrated Circuits</b>	192
	I. Ribeiro, G. Wirth, and F. G. L. Kastensmidt	
<b>PC3.</b>	<b>Transient Response of 3-D Multi-Channel Nanowire MOSFETs Submitted to Heavy Ion Irradiation: a 3-D Simulation Study</b>	198
	D. Munteanu, and J.-L. Autran	
<b>PC5LN.</b>	<b>A 3-D Simulation Study about Single Event Gate Damage in Medium Voltage Power MOSFET</b>	209
	A. Porzio, F. Velardi, G. Busatto, F. Iannuzzo, A. Sanseverino, and G. Currò	

## SESSION D. DOSIMETRY AND FACILITIES

<b>PD5LN. Characterization of the ANITA Neutron Source for Accelerated SEE Testing at The Svedberg Laboratory . . . . .</b>	<b>260</b>
A. V. Prokofiev, J. Blomgren, R. Nolte, S. P. Platt, S. Röttger, and A. N. Smirnov	

## SESSION E. HARDNESS BY DESIGN

<b>E1. The Path and Challenges to 90nm Radiation Hardened Technology . . . . .</b>	<b>269</b>
N. Haddad, E. Chan, S. Doyle, A. Kelly, R. Lawrence, D. Lawson, D. Patel, and J. Ross	
<b>E3. 3-D Simulation Analysis of Bipolar Amplification in Planar Double-Gate and FinFET with Independent Gates . . . . .</b>	<b>280</b>
D. Munteanu, J.-L. Autran, and M. Moreau	
<b>E4. Automatic Insertion of Selective TMR for SEU Mitigation . . . . .</b>	<b>284</b>
O. Ruano, P. Reviriego, and J. A. Maestro	
<b>E5. Mitigating Soft Errors in SRAM-based FPGAs by Using Large Grain TMR with Selective Partial Reconfiguration . . . . .</b>	<b>288</b>
J. R. Azambuja, C. Pilotto, and F. G. L. Kastensmidt	
<b>PE2. Using FLIPPER to Predict Irradiation Results for VIRTEX 2 Devices . . . . .</b>	<b>300</b>
M. Alderighi, F. Casini, M. Citterio, S. D'Angelo, M. Mancini, S. Pastore, G. R. Sechi, and G. Sorrenti	
<b>PE4. Recent Progress in CERN RD39: Radiation Hard Cryogenic Silicon Detectors for Applications in LHC Experiments and Their Future Upgrades . . . . .</b>	<b>311</b>
E. Tuominen, P. Anbinderis, T. Anbinderis, R. Bates, W. de Boer, E. Borchi, M. Bruzzi, C. Buttar, W. Chen, V. Cindro, S. Czellar, V. Eremin, A. Furgeri, E. Gaubas, J. Härkönen, E. Heijne, I. Ilyashenko, V. Kalesinskas, M. J. Kortelainen, M. Krause, T. Lampén, Z. Li, P. Luukka, I. Mandić, D. Menichelli, M. Mikuz, O. Militaru, S. Mueller, T. Mäenpää, T. O. Niinikoski, V. O'Shea, C. Parkes, K. Piotrzkowski, S. Pirolo, P. Pusa, J. Räisänen, X. Rouby, E. Tuovinen, J. Vaitkus, E. Verbitskaya, S. Väyrynen, and M. Zavrtanik	

<b>PE7LN. Multiple SEU Tolerance in LUTs of FPGAs Using Protected Schemes . . . . .</b>	<b>325</b>
C. Argyrides, H. Zarandi, and D. K. Pradhan	

## SESSION F. PHOTONICS DEVICES AND ICs

<b>F1. TID Effects in Deep N-well CMOS Monolithic Active Pixel Sensors . . . . .</b>	<b>332</b>
L. Ratti, C. Andreoli, L. Gaioni, M. Manghisoni, E. Pozzati, V. Re, and G. Traversi	
<b>F2. Multi Level RTS in Proton Irradiated CMOS Image Sensors Manufactured in Deep Sub-micron Technology . . . . .</b>	<b>338</b>
V. Goiffon, G. R. Hopkinson, P. Magnan, F. Bernard, G. Rolland, and O. Saint-Pé	
<b>F3. Analysis of CCD Dark Current Degradation in Orbit . . . . .</b>	<b>344</b>
A. Penquer, M. Boutillier, G. Rolland, and O. Gilard	
<b>F4. Radiation Tolerance Tests of Small-Sized CsI(Tl) Scintillators Coupled to Photodiodes . .</b>	<b>350</b>
E. Valtonen, J. Peltonen, O. V. Dudnik, A. M. Kudin, H. Andersson, Yu. A. Borodenko, T. Eronen, J. Huovelin, H. Kettunen, E. V. Kurbatov, J. Lehti, S. Nenonen, M. Rossi, R. Vainio, and A. Virtanen	
<b>PF3LN. Charge-Coupled Device Proton-Induced Degradation Observed on Low Earth Orbit Star Tracker . . . . .</b>	<b>370</b>
M. Beaumel, D. Hervé, and L. Paganelli-Pradere	

## SESSION G. HARDNESS ASSURANCE

<b>G1. Laser Simulation of SEE Due to Localized Ionization in Dielectric Structures . . . . .</b>	<b>381</b>
A. M. Chugg, R. English, S. Parker, and A. J. Burnell	
<b>G3. A Technique to Calculate the MBU Distribution of a Memory under Radiation Suffering the Event Accumulation Problem . . . . .</b>	<b>393</b>
P. Reviriego, and J. A. Maestro	
<b>PG2. Smart Behavioral Netlist Simulation for SEU Protection Verification . . . . .</b>	<b>406</b>
S. Schulz, G. Beltrame, and D. Merodio-Codinachs	
<b>PG4. Assessing and Mitigating Radiation Effects in Xilinx SRAM FPGAs . . . . .</b>	<b>418</b>
P. C. Adell, G. R. Allen, G. Swift, and S. McClure	

## SESSION H. BASIC MECHANISMS

<b>H2.</b>	<b>Dose Enhancement due to Interconnects in Deep-Submicron MOSFETs Exposed to X-Rays</b>	<b>432</b>
	A. Griffoni, M. Silvestri, S. Gerardin, G. Meneghesso, A. Paccagnella, B. Kaczer, M. de Potter de ten Broeck, R. Verbeeck, and A. Nackaerts	
<b>H5.</b>	<b>Heavy Ion Irradiation Effects on Capacitors with SiO<sub>2</sub> and ONO as Dielectrics . . . . .</b>	<b>447</b>
	A. Gasperin, A. Paccagnella, G. Ghidini, and A. Sebastiani	
<b>PH3.</b>	<b>Experimental Linear Energy Transfer of Heavy Ions in Silicon for RADEF Cocktail Species</b>	<b>470</b>
	A. Javanainen, M. Sillanpää, W. H. Trzaska, A. Virtanen, G. Berger, W. Hajdas, R. Harboe-Sørensen, H. Kettunen, T. Malkiewicz, M. Mutterer, J. Perkowski, A. Pirojenko, I. Riihimäki, T. Sajavaara, G. Tyurin, and H. J. Whitlow	
<b>PH6LN.</b>	<b>Influences of Cluster Related Defects on Silicon Detector Properties . . . . .</b>	<b>485</b>
	A. Junkes, E. Fretwurst, and I. Pintilie	

## SESSION J. RADIATION ENVIRONMENTS AND EFFECTS

<b>J3.</b>	<b>Optimization Using Monte Carlo Calculations of a Bonner Spheres Spectrometer Extended to High Energies for the Neutron Environments Characterization . . . . .</b>	<b>504</b>
	S. Serre, K. Castellani-Coulié, D. Paul, and V. Lacoste	
<b>PJ1LN.</b>	<b>Altitude and Underground Real-Time SER Characterization of CMOS 65 nm SRAM . . .</b>	<b>519</b>
	J. L. Autran, P. Roche, S. Sauze, G. Gasiot, D. Munteanu, P. Loaiza, M. Zampaolo, and J. Borel	
<b>Author Index</b>	<b>525</b>	
<b>List of Attendees</b>	<b>530</b>	
<b>Announcement of RADECS 2009</b>	<b>541</b>	